

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC4497

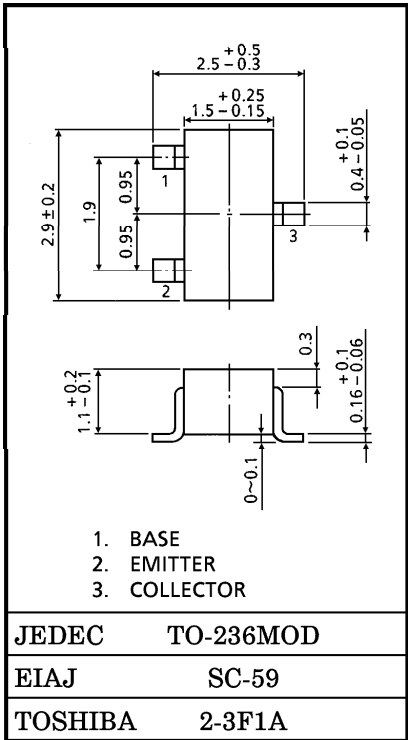
HIGH VOLTAGE CONTROL APPLICATIONS

- High Voltage : $V_{CBO}=300V$, $V_{CEO}=300V$
- Low Saturation Voltage : $V_{CE(sat)}=0.5V$ (Max.)
- Small Collector Output Capacitance : $C_{ob}=3pF$ (Typ.)
- Complementary to 2SA1721

MAXIMUM RATINGS ($T_a = 25^{\circ}C$)

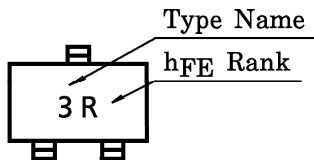
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	$-55\sim150$	$^{\circ}C$

Unit in mm



Weight : 0.012g

MARKING



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 300V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR) CBO}$	$I_C = 0.1mA, I_E = 0$	300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 1mA, I_B = 0$	300	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 10V, I_C = 20mA$	30	—	150	
	$h_{FE(2)}$	$V_{CE} = 10V, I_C = 1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$	—	—	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20mA, I_B = 2mA$	—	—	1.2	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 10mA$	—	70	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 20V, I_E = 0, f = 1MHz$	—	3	4	pF

(Note) : $h_{FE(1)}$ Classification R : 30~90, O : 50~150

